

• General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

• Features

- Low  $R_{DS(ON)}$  to minimize conductive loss
- High GOX reliability
- Low Thermal resistance

• Application

- BLDC Motor driver
- DC-DC
- Load Switch

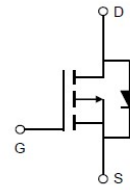
• Ordering Information:

Part NO.	ZM930P06T
Marking	930P06
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

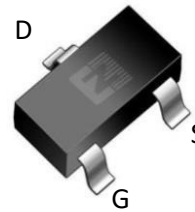
• Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	$V_{DS}$	$25^\circ\text{C} \leq T_J \leq 150^\circ\text{C}$	-60	V
Gate-Source Voltage	$V_{GS}$		$\pm 20$	V
Continuous Drain Current	$I_D$	$T_C=25^\circ\text{C}$	-2.0	A
	$I_D$	$T_C=75^\circ\text{C}$	-1.98	A
	$I_D$	$T_C=100^\circ\text{C}$	-1.59	A
Pulsed Drain Current	$I_{DM}$	Pulsed; $t_p \leq 10 \mu\text{s}$ ; $T_{mb} = 25^\circ\text{C}$ ;	-8	A
Total Power Dissipation	$P_D$	$T_C=25^\circ\text{C}$	2	W
Total Power Dissipation	$P_D$	$T_A=25^\circ\text{C}$	0.7	W
Operating Junction Temperature	$T_J$		-55 to +150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$		-55 to +150	$^\circ\text{C}$
Single Pulse Avalanche Energy	$E_{AS}$	L=0.1mH, VGS=10V, Rg=25 $\Omega$ ,	1.2	mJ
		L=0.5mH, VGS=10V, Rg=25 $\Omega$ ,	2.52	mJ
ESD Level (HBM)			CLASS 2	

• Product Summary



$V_{DS} = -60\text{V}$   
 $R_{DS(ON)} = 103\text{m}\Omega$   
 $I_D = -2\text{A}$



SOT-23-3



**•Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$		-	80	°C/W
Thermal resistance, junction-ambient <sup>①</sup>	$R_{thJA}$		-	180	°C/W
Soldering temperature	$T_{sold}$		-	260	°C

**•Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	-60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	-1.3	-1.8	-2.5	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{GS} = 0V, V_{DS} = -60V$			1.0	$\mu A$
Gate- Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = -1.5A$		103	130	m $\Omega$
		$V_{GS} = 4.5V, I_D = -1A$		128	166	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{GS} = 5V, I_{SD} = -1A$		20		S
Diode Forward Voltage	$V_{FSD}$	$V_{GS} = 0V, I_{SD} = -1.5A$			1.3	V

**•Dynamic characteristics**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	
Input capacitance	$C_{iss}$	$f = 1MHz, V_{DS} = -25V$	-	650	-	pF	
Output capacitance	$C_{oss}$		-	95	-		
Reverse transfer capacitance	$C_{rss}$		-	70	-		
Gate Resistance	$R_g$	$f = 1MHz$	-	8		$\Omega$	
Total gate charge	$Q_g$	$V_{DD} = -15V, I_D = -1A, V_{GS} = -10V$	-	12	-	nC	
	$Q_g(-4.5V)$		-	21	-		
	Gate - Source charge		$Q_{gs}$	-	1.6		-
	Gate - Drain charge		$Q_{gd}$	-	2.6		-
Turn-ON Delay time	$t_{D(on)}$	$V_{GS} = -10V, V_{DS} = -15V, R_G = 3.3\Omega, I_D = -1A$	-	6.5	-	ns	
Turn-ON Rise time	$t_r$		-	8	-	ns	
Turn-Off Delay time	$t_{D(off)}$		-	16.5	-	ns	
Turn-Off Fall time	$t_f$		-	4	-	ns	
Reverse Recovery Time	$t_{RR}$	$V_{DD} = -20V, dI_S/dt = 100A/\mu s, I_S = -2A$	-	55	-	ns	
Reverse Recovery Charge	$Q_{RR}$		-	136	-	nC	

Fig.1 Gate-Charge Characteristics

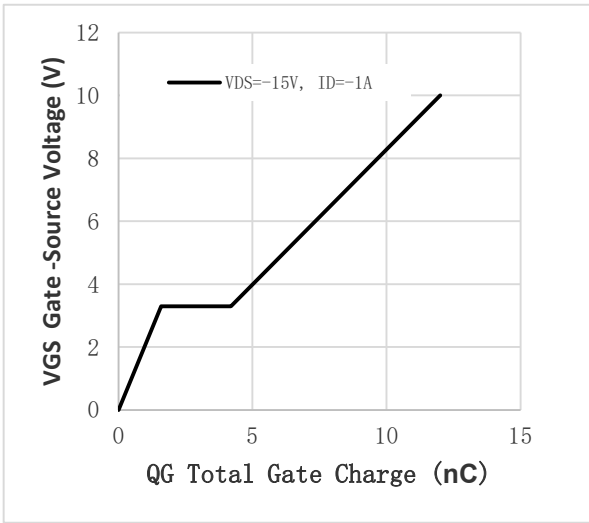


Fig.2 Capacitance Characteristics

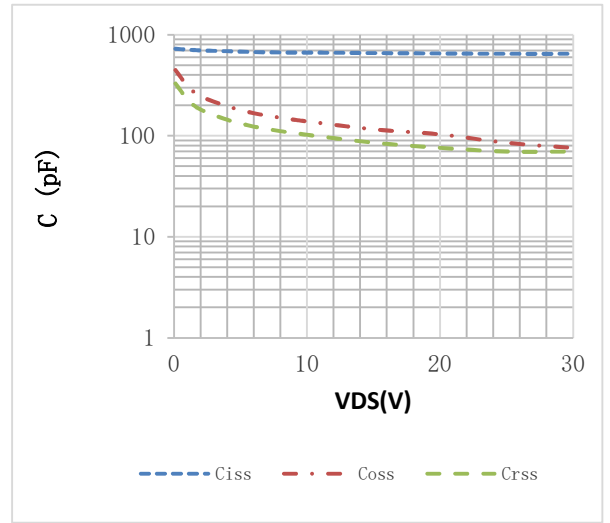


Fig.3 Power Dissipation

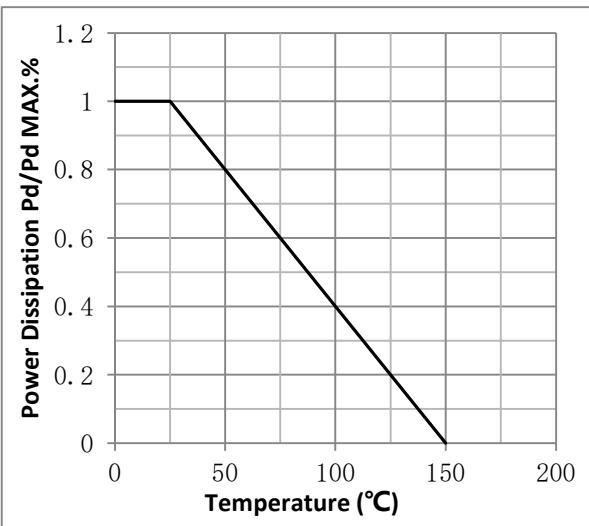


Fig.4 Typical output Characteristics

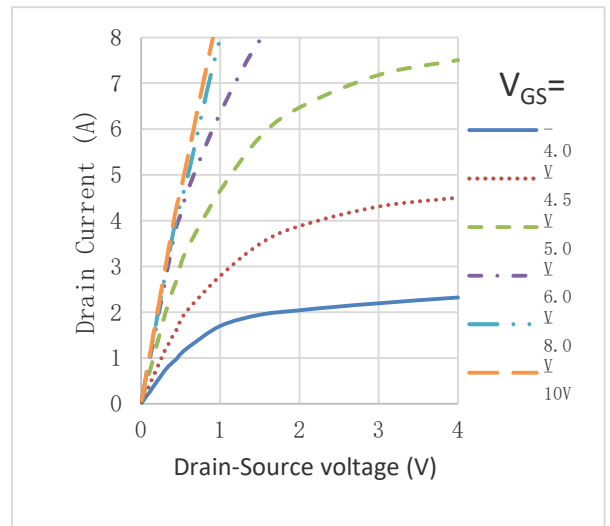


Fig.5 Threshold Voltage V.S Junction Temperature

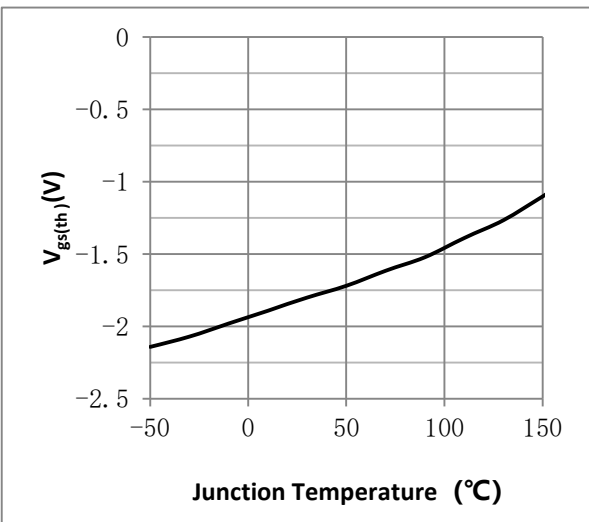


Fig.6 Resistance V.S Drain Current

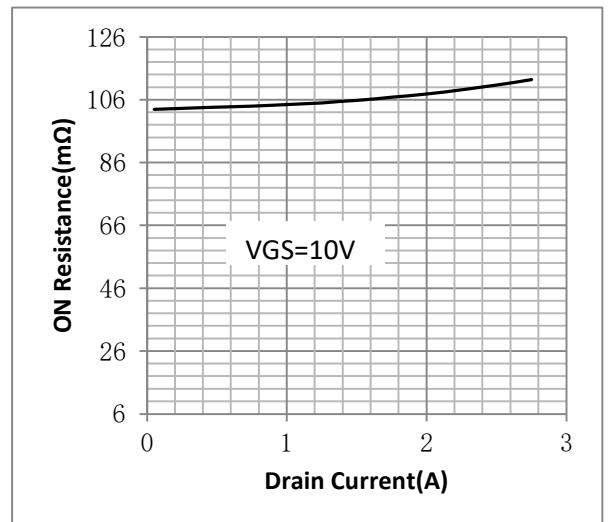


Fig.7 On-Resistance VS Gate Source Voltage

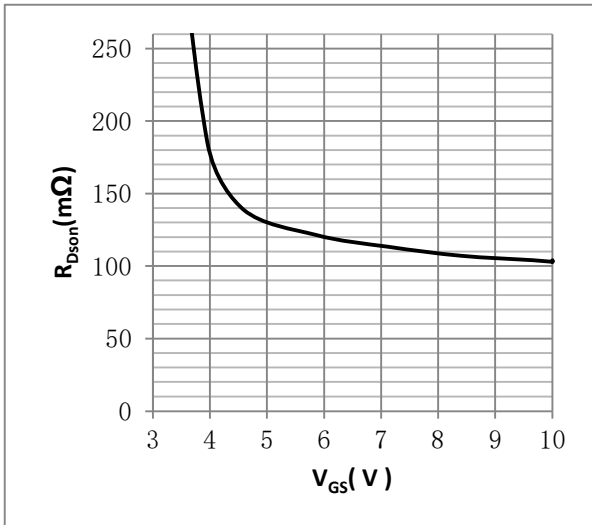


Fig.8 On-Resistance V.S Junction Temperature

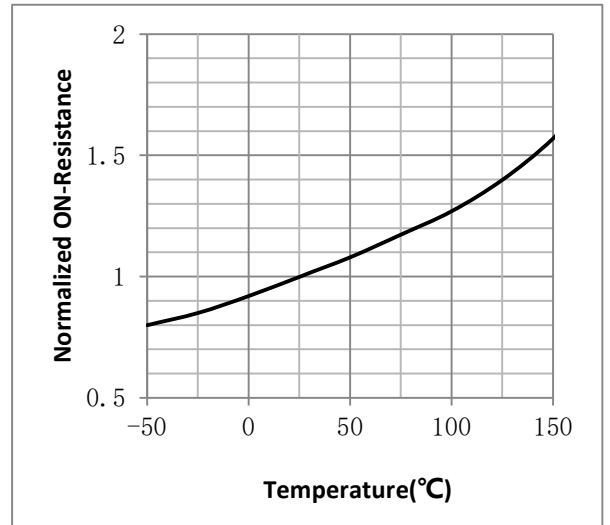


Figure 9. Diode Forward Voltage vs. Current

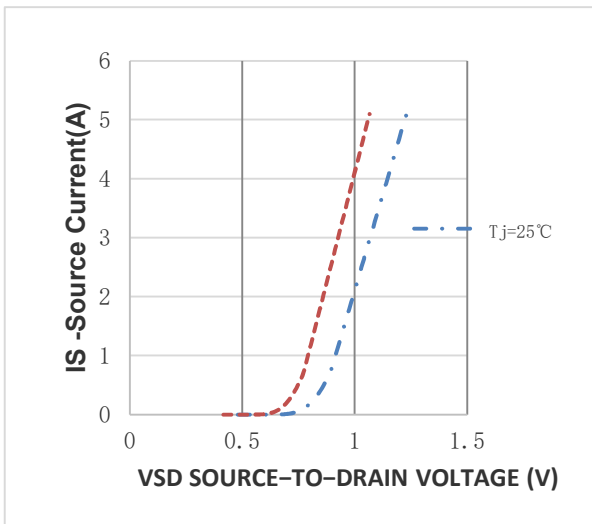


Figure 10. Transfer Characteristics

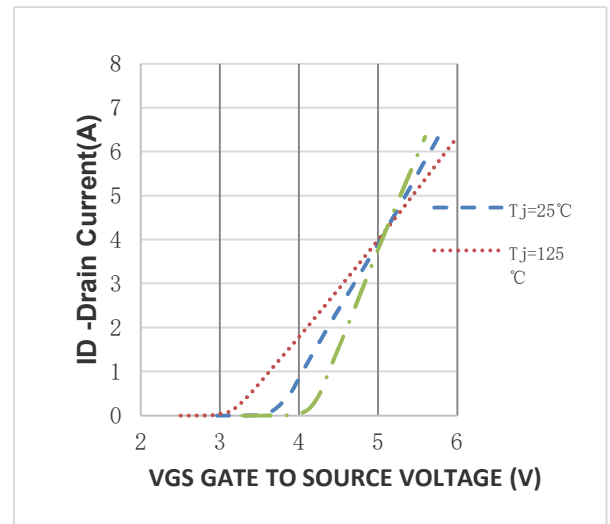


Fig.11 SOA Maximum Safe Operating Area

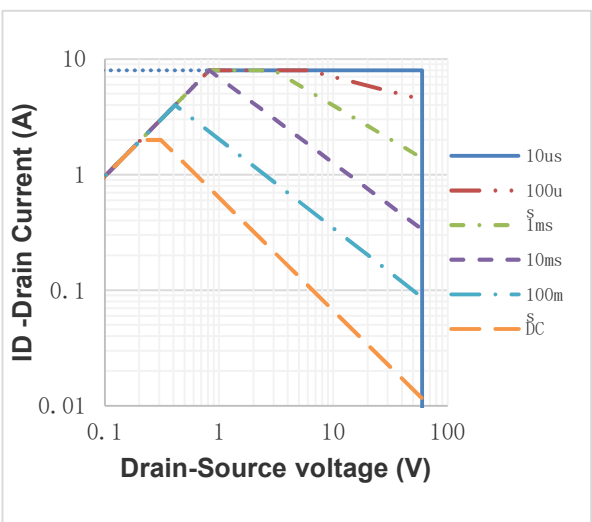
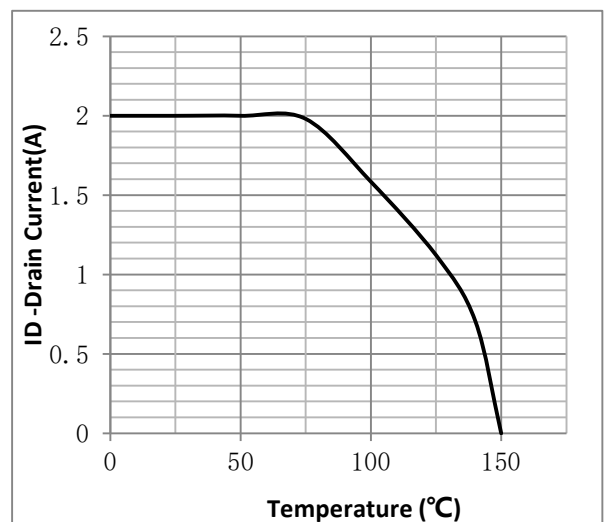
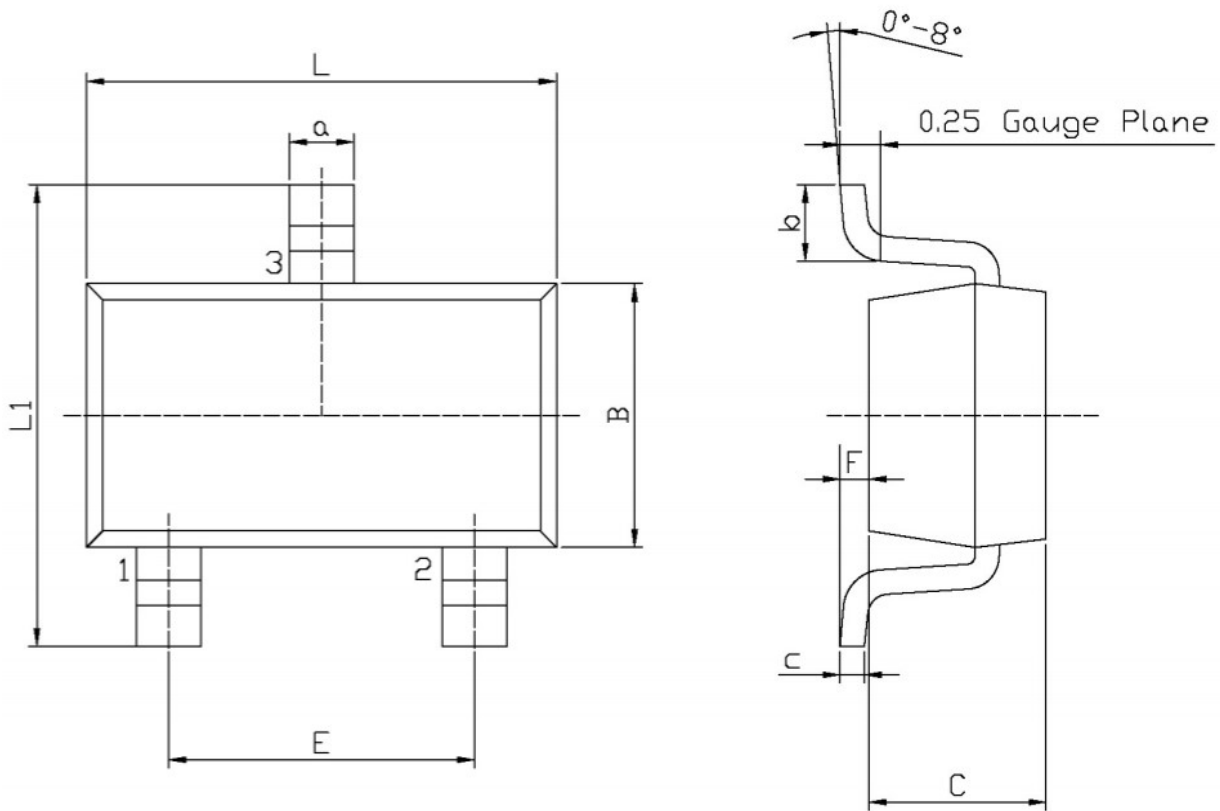


Fig.12 ID vs. Case Temperature<sup>②</sup>



•SOT-23-3 Package Outline



Unit: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
L	2.82	3.02	a	0.35	0.50
B	1.50	1.70	c	0.10	0.20
C	0.90	1.30	b	0.35	0.55
L1	2.60	3.00	F	0	0.15
E	1.80	2.00			

**Note:**

- ① Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ② Practically the current will be limited by PCB, thermal design and operating temperature. VGS=10V.

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## Revision History

Version	Date	Change
A	2019. 3. 6	NEW
B	2021. 9. 7	1. Add Reach, HF figure
C	2022. 9. 9	1. Add Dynamic characteristics
D	2022. 10. 30	Add SOA/ID Figure
E	2024. 5. 20	Modify curves.